

NTE1828 Integrated Circuit Quad Transistor Array, 10kΩ

Features:

- 4 Circuits
- Output Current: $I_C = 50\text{mA}$
- Breakdown Voltage: $V_{CEO} = 24\text{V}$
- Built-In Base Current Limiting Resistor

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector–Base Voltage, V_{CBO}	50V
Collector–Emitter Voltage, V_{CEO}	24V
Collector Substrate Voltage, V_{CIO}	50V
Collector Current, I_C	50mA
Input Voltage, V_1	–0.5V to 50V
Collector Power Dissipation (Per Transistor), P_C	250mW
Power Dissipation, P_D	1000mW
Operating Ambient Temperature Range, T_{opr}	–30° to +75°C
Storage Temperature Range, T_{stg}	–55° to +150°C

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Base Voltage	V_{CBO}	$I_C = 10\mu\text{A}$, $I_E = 0$	50	–	–	V
Collector–Emitter Voltage	V_{CEO}	$I_C = 1\text{mA}$, $I_B = 0$	24	–	–	V
Collector Leakage Current	I_{CEO}	$V_{CE} = 10\text{V}$, $R_{BE} = \infty$	–	–	1	μA
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 5\text{mA}$, $I_I = 0.6\text{mA}$	–	0.1	0.2	V
		$I_C = 25\text{mA}$, $I_I = 2.6\text{mA}$	–	0.3	0.4	V
Input Voltage	V_1	$V_{CE} = 300\text{mV}$, $I_C = 5\text{mA}$	–	2.2	3.3	V
		$V_{CE} = 500\text{mV}$, $I_C = 25\text{mA}$	–	5.6	10	V
Input Current	I_I	$I_C = 5\text{mA}$, $V_1 = 5\text{V}$	–	0.45	0.60	mA
		$I_C = 25\text{mA}$, $V_1 = 15\text{V}$	–	1.6	2.0	mA

Pin Connection Diagram (Front View)

